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AMENDMENT TRANSMITTAL LETTER				Docket No. 101361-0043	
Application No. 09/884,451-Conf. #1957		Filing Date June 19, 2001		Examiner J. Maldonado	
				Art Unit 2823	
Applicant(s): Robert P. Dolan, Bernhard F. Cordts, III, and Malvin Farley					
Invention: SIMOX USING CONTROLLED WATER VAPOR FOR OXYGEN IMPLANTS					
TO THE COMMISSIONER FOR PATENTS					
Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.					
CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	13	- 20 =		x	0.00
Independent Claims	2	- 3 =		x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity					
<input checked="" type="checkbox"/> No additional fee is required for this amendment.					
<input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of \$ _____. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge and credit Deposit Account No. <u>141449</u> as described below. A duplicate copy of this sheet is enclosed.					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 Reza Mollaaghababa Attorney Reg. No.: 43,810 NUTTER MCCLENNEN & FISH LLP World Trade Center West 155 Seaport Boulevard Boston, Massachusetts 02110-2699 617-439-2514				Dated: <u>February 24, 2003</u>	
Amendment Transmittal					
I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail, in an envelope addressed to: Box Non-Fee Amendment, Commissioner for Patents, Washington, DC 20231, on the date shown below.					
Dated: February 24, 2003		Signature: (Reza Mollaaghababa)			

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Dated: February 24, 2003

Signature

(Reza Mollaaghababa)

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Docket No.: 101361-0043
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Robert P. Dolan, et al

Application No.: 09/884,451

Group Art Unit: 2823

Filed: June 19, 2001

Examiner: Julio J. Maldonado

For: SIMOX USING CONTROLLED WATER
VAPOR FOR OXYGEN IMPLANTS

AMENDMENT AND RESPONSE UNDER 37 CFR 1.116

Box AF
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action mailed on December 13, 2002 from the United States Patent and Trademark Office in the above-referenced patent application, Applicants provide the following amendments and remarks. In addition to a marked-up copy of the amended claim in which additions are underlined and deletions are bracketed, a clean copy of all claims presently under examination is also provided.

Claims 1-19 are pending in the application. The Office Action considers claims 14-19, directed to a system for producing SIMOX wafers, presented as new claims in a response filed on October 3, 2003 to the previous Office Action, as being directed to a non-elected invention. Hence, only claims 1-13 have been subjected to examination in the present Office Action.

As discussed in more detail below, claims 1-13 are now believed to be in condition for allowance because none of the cited references teaches utilizing a fluid other than pure molecular oxygen as a *background gas during* an ion implantation step of a method of processing a silicon substrate to inhibit formation of threading dislocations in a top silicon layer formed in the

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